

2N7000 2N7002

N-channel 60 V, 1.8 Ω, 0.35 A, SOT23-3L, TO-92 STripFET™ Power MOSFET

Features

Туре	V _{DSS}	R _{DS(on)} max	I _D
2N7000	60 V	< 5 Ω(@10V)	0.35 A
2N7002	60 V	< 5 Ω(@10V)	0.20 A

- Low Q_a
- Low threshold drive

Application

Switching applications

Description

This Power MOSFET is the second generation of STMicroelectronics unique "single feature size" strip-based process. The resulting transistor shows extremely high packing density for low onresistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

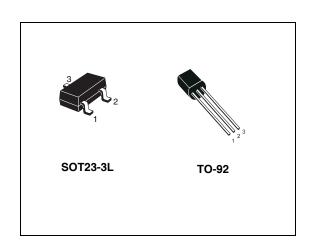


Figure 1. Internal schematic diagram

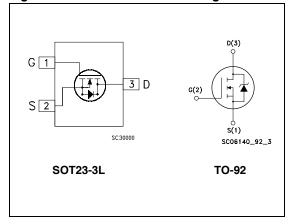


Table 1. Device summary

Order codes	Marking	Package	Packaging
2N7000	2N7000G	TO-92	Bulk
2N7002	ST2N	SOT23-3L	Tape and reel

November 2008 Rev 9 1/14

Contents 2N7000, 2N7002

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2N7000, 2N7002 Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
	Farameter	TO-92		
V_{DS}	Drain-source voltage (V _{GS} = 0) 60		0	V
V_{DGR}	Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$) 60		٧	
V _{GS}	Gate- source voltage ± 18		18	V
I _D	Drain current (continuous) at $T_C = 25$ °C	0.35	0.20	Α
I _{DM} ⁽¹⁾	Drain current (pulsed)	1.4	1	Α
P _{TOT}	Total dissipation at T _C = 25 °C	1	0.35	W

^{1.} Pulse width limited by safe operating area

Table 3. Thermal data

Symbol	Parameter	Value		Unit
Symbol	raiametei	TO-92	SOT23-3L	
Rthj-amb	Thermal resistance junction-ambient max 125 357		357.1 ⁽¹⁾	°C/W
T _J	Operating junction temperature - 55 to 150		°C	
T _{stg}	Storage temperature	- 55 (0 130	

^{1.} When mounted on 1inch² FR-4, 2 Oz copper board.

Electrical characteristics 2N7000, 2N7002

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 250 μA, V _{GS} =0	60			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V_{DS} = max rating V_{DS} = max rating, T_{C} = 125 °C			1 10	μ Α μ Α
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 18 V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	2.1	3	V
R _{DS(on)}	Static drain-source on resistance	$V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 0.5 \text{ A}$		1.8 2	5 5.3	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
9 _{fs} (1)	Forward transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 0.5 \text{ A}$		0.6		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25 \text{ V, f} = 1 \text{ MHz,}$ $V_{GS} = 0$		43 20 6		pF pF pF
$\begin{array}{c} t_{d(on)} \\ t_{r} \\ t_{d(off)} \\ t_{f} \end{array}$	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 30 \text{ V}, I_{D} = 0.5 \text{ A}$ $R_{G} = 4.7 \Omega V_{GS} = 4.5 \text{ V}$ (see <i>Figure 16</i>)		5 15 7 8		ns ns ns
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 30 \text{ V}, I_D = 1 \text{ A},$ $V_{GS} = 5 \text{ V}$ (see Figure 17)		1.4 0.8 0.5	2	nC nC nC

^{1.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%.

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current Source-drain current (pulsed)				0.35 1.40	A A
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 1 A, V _{GS} = 0			1.2	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 1$ A, di/dt = 100 A/ μ s, $V_{DD} = 20$ V, $T_j = 150$ °C (see <i>Figure 18</i>)		32 25 1.6		ns nC A

^{1.} Pulse width limited by safe operating area.

^{2.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%

Electrical characteristics 2N7000, 2N7002

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-92

Figure 3. Thermal impedance for TO-92

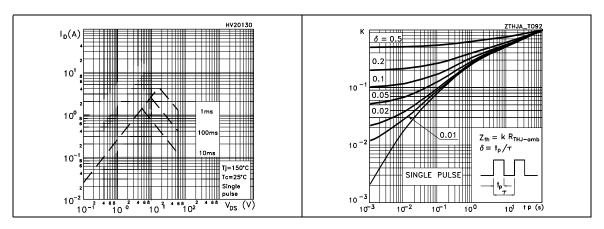


Figure 4. Safe operating area for SOT23-3L

Figure 5. Thermal impedance for SOT23-3L

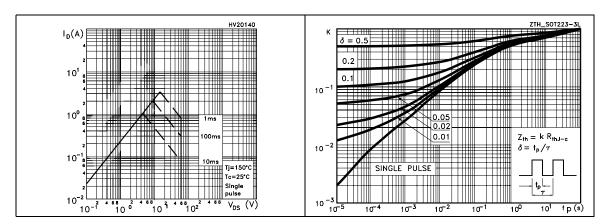
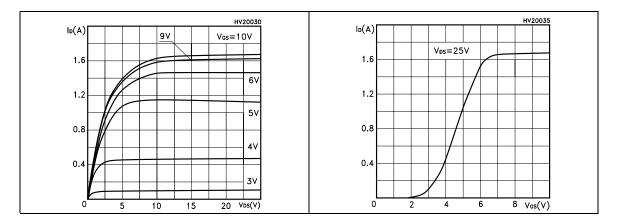


Figure 6. Output characteristics

Figure 7. Transfer characteristics



2N7000, 2N7002 Electrical characteristics

Figure 8. Transconductance

Figure 9. Static drain-source on resistance

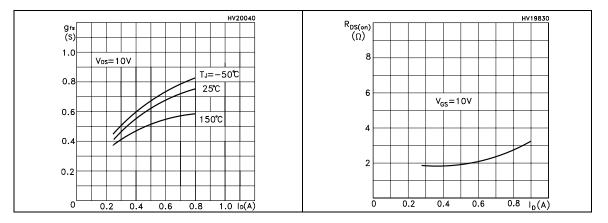


Figure 10. Gate charge vs gate-source voltage Figure 11. Capacitance variations

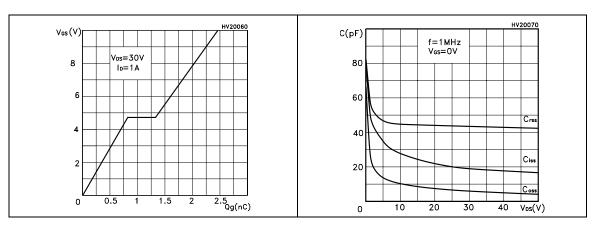
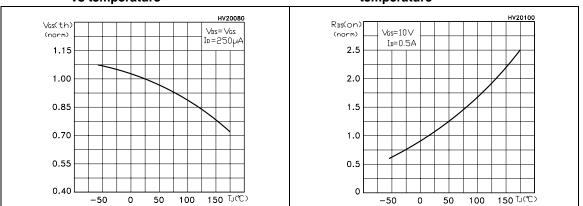


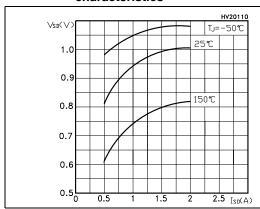
Figure 12. Normalized gate threshold voltage Figure 13. Normalized on resistance vs vs temperature temperature

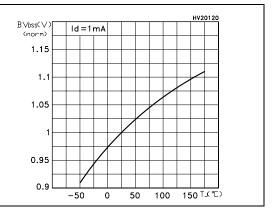


Electrical characteristics 2N7000, 2N7002

Figure 14. Source-drain diode forward characteristics

Figure 15. Normalized B_{VDSS} vs temperature





2N7000, 2N7002 Test circuits

3 Test circuits

Figure 16. Switching times test circuit for resistive load

Figure 17. Gate charge test circuit

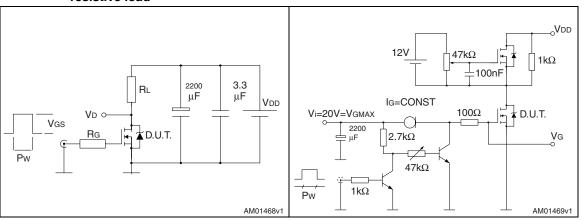


Figure 18. Test circuit for inductive load switching and diode recovery times

Figure 19. Unclamped Inductive load test circuit

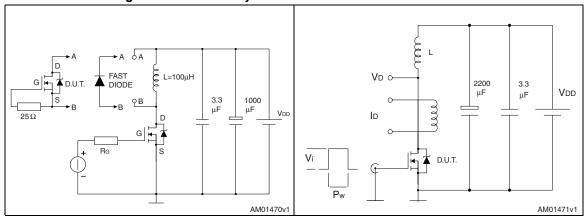
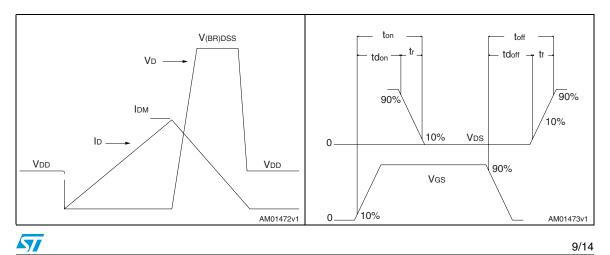


Figure 20. Unclamped inductive waveform

Figure 21. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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Table 7. TO-92 mechanical data

Dim.		mm	
Dilli.	Min.	Тур.	Max.
А	4.32		4.95
b	0.36		0.51
D	4.45		4.95
E	3.30		3.94
е	2.41		2.67
e1	1.14		1.40
L	12.70		15.49
R	2.16		2.41
S1	0.92		1.52
W	0.41		0.56
V		5°	

Figure 22. TO-92 drawing

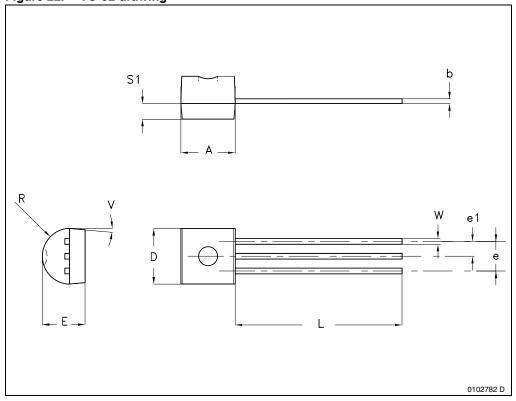
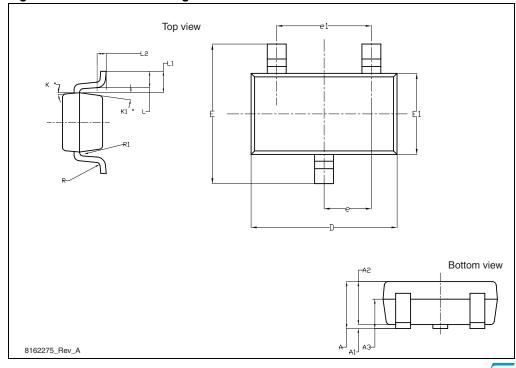


Table 8. SOT23-3L mechanical data

Dim.		mm	
Dilli.	Min.	Тур.	Max.
Α			1.25
A1	0		0.15
A2	1.00		1.20
А3	0.60		0.70
D	2.826		3.026
E	2.60		3.00
E1	1.526		1.726
е		0.95	
e1		1.90	
L	0.35		0.60
L1		0.59	
L2		0.25	
R	0.05		
R1	0.05		0.20
K	3°		7°
K1	6°		10°

Figure 23. SOT23-3L drawing



2N7000, 2N7002 Revision history

5 Revision history

Table 9. Document revision history

Date	Revision	Changes
09-Oct-2004	1	First document
22-Jun-2004	2	Complete document
06-Apr-2005	3	New typ and max value inserted for Vgs(th)
19-Apr-2005	4	The document has been reformatted
26-Apr-2005	5	New Pin configuration for TO-92
28-Apr-2005	6	Pin configuration change again
19-Jun-2006	7	New template, no content change
03-Sep-2007	8	Corrected marking on first page
04-Nov-2008	9	 Updated Table 7: TO-92 mechanical data and Figure 22: TO-92 drawing. Updated Table 8: SOT23-3L mechanical data and Figure 23: SOT23-3L drawing.

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